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February 7, 2001

TO: Commissioner for Patents
 Attn: George C. Eckert II
 Patent Examining Corps
 Facsimile Center
 Washington, D.C. 20231

FROM: Robert E. MatesOUR REF: 303.356US1TELEPHONE: (612) 373-6973FAX NUMBER (703) 305-3431

* Please deliver to Examiner George C. Eckert II in Art Unit 2815. *

Document(s) Transmitted: Amendment and Response Under 37 CFR 1.116 (20 pgs)Total pages of this transmission, including cover letter: 21 pgs

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In re. Patent Application of: Leonard Forbes et al.Examiner: George C. Eckert IISerial No.: 08/902,133Group Art Unit: 2815Filed: July 29, 1997Docket No.: 303.356US1

Title: DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY
 MEMORY DEVICE

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By: [Signature]Name: Robert E. MatesReg. No.: Reg. No. 35,271

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EXPEDITED PROCEDURE - EXAMINING GROUP 2815

S/N 08/902,133PATENTIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: George C. Eckert II

Serial No.: 08/902,133

Group Art Unit: 2815

Filed: July 29, 1997

Docket: 303.356US1

Title: DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ
ONLY MEMORY DEVICEAMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116Box AF
Commissioner for Patents
Washington, D.C. 20231In response to the final Office Action dated 20 September 2000, please amend the
application as follows:IN THE CLAIMS

Please cancel claims 1, 7, 11, 16, 33, and 38.

Please amend the claims as follows:

2. [Amended] The memory cell of claim [1] 2, wherein materials comprising at least one
of the storage electrode and the insulator are selected to have an electron affinity causing the
barrier energy to be selected at less than approximately 3.3 eV.

6. [Amended] The memory cell of claim [1] 2, wherein the insulator comprises a material
that has a material composition that is selected to obtain a larger electron affinity than silicon
dioxide.

7. [Amended] The memory cell of claim [1] 2, wherein the barrier energy is less than
approximately 2.0 eV.

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